

N-Channel 130 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)		
130	0.0048 at V _{GS} = 10 V	128 ^a		

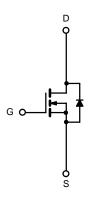
FEATURES

- DT-Trench Power MOSFET
- New Package with Low Thermal Resistance
- 100 % R_g Tested









N-Channel MOSFET

ABSOLUTE MAXIMUM RATI	NGS $T_C = 25 ^{\circ}C$, unless oth	erwise noted			
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V _{DS}	130	V		
Gate-Source Voltage	V_{GS}	± 20			
Continuous Drain Current /T 475 °C)	T _C = 25 °C	,	128 ^a	Α	
Continuous Drain Current ($T_J = 175 ^{\circ}\text{C}$)	T _C = 125 °C	l _D	92 ^a		
Pulsed Drain Current	I _{DM}	460			
Avalanche Current	I _{AR}	85			
Repetitive Avalanche Energy ^b	L = 0.1 mH	E _{AR}	280	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	В	375 ^c	W	
	T _A = 25 °C	P_{D}	3.95] vv	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Limit	Unit	
Junction-to-Ambient	PCB Mount (TO-263) ^d	R _{thJA}	40	°C/W	
Junction-to-Case (Drain)		R _{thJC}	0.4	C/VV	

Notes:

- a. Package limited.
- b. Duty cycle ≤ 1 %.
- c. See SOA curve for voltage derating.
 d. When mounted on 1" square PCB (FR-4 material).



SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	$V_{DS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	130			V
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2		4	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
		V _{DS} = 100 V, V _{GS} = 0 V			1	μΑ
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V, T _J = 125 °C			50	
		V _{DS} = 100 V, V _{GS} = 0 V, T _J = 175 °C			250	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	120			Α
		V _{GS} = 10 V, I _D = 60 A		0.0048	0.0055	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 30 A, T _J = 125 °C			0.0089	Ω
		V _{GS} = 10 V, I _D = 30 A, T _J = 175 °C			0.0135	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 30 A	25			S
Dynamic ^b						
Input Capacitance	C _{iss}			6200		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		930		
Reverse Transfer Capacitance	C _{rss}			420		
Total Gate Charge ^c	Qg			130	160	nC
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 85 \text{ A}$		24		
Gate-Drain Charge ^c	Q _{gd}			24		
Gate Resistance	R _g		1.0		6.2	Ω
Turn-On Delay Time ^c	t _{d(on)}			20	30	
Rise Time ^c	t _r	V_{DD} = 50 V, R_L = 0.6 Ω $I_D \cong$ 85 A, V_{GEN} = 10 V, R_g = 2.5 Ω		125	200	ns
Turn-Off Delay Time ^c	t _{d(off)}			55	85	
Fall Time ^c	t _f			130	195	
Source-Drain Diode Ratings and Cha	aracteristics -	Γ _C = 25 °C ^b		•		
Continuous Current	I _S				118	А
Pulsed Current	I _{SM}				440	
Forward Voltage ^a	V_{SD}	I _F = 85 A, V _{GS} = 0 V		1.0	1.5	V
Reverse Recovery Time	t _{rr}			70	140	ns
Peak Reverse Recovery Charge	I _{RM(REC)}	I _F = 50 A, dI/dt = 100 A/μs		5.5	10	Α
Reverse Recovery Charge	Q _{rr}			0.19	0.35	μC

Notes:

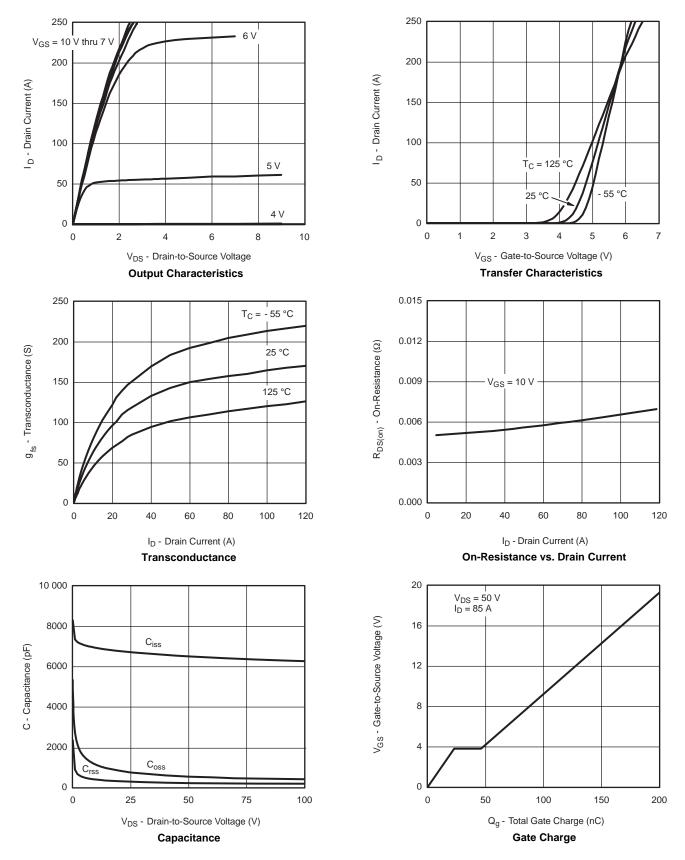
- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



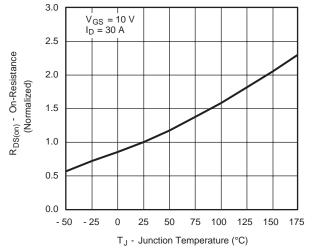


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

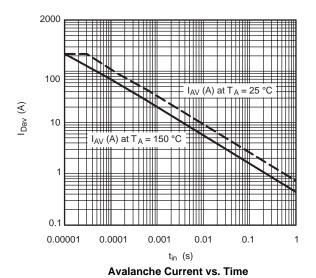




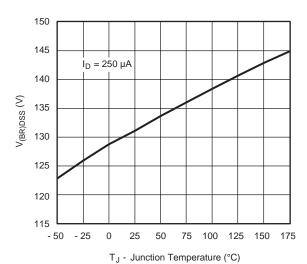
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

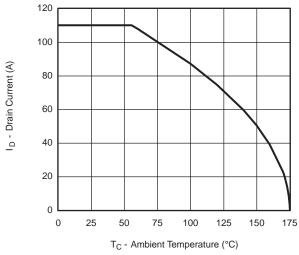


Drain Source Breakdown vs. Junction Temperature



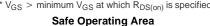


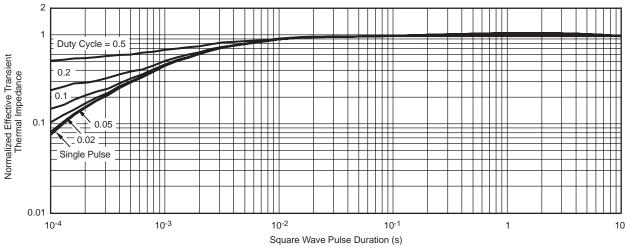
THERMAL RATINGS



1000 200 I_D - Drain Current (A) by R_{DS(on)*} 10 100 ms, DC T_C = 25 °C Single Pulse 0.1 0.1 1000 10 130 V_{DS} - Drain-to-Source Voltage (V) * V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Maximum Avalanche and Drain Current vs. Case Temperature





Normalized Thermal Transient Impedance, Junction-to-Case





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